ABSTRACT OF THE DISCLOSURE

In one aspect, the invention encompasses a semiconductor processing method wherein a conductive copper-containing material is formed over a semiconductive substrate and a second material is formed proximate the conductive material. A barrier layer is formed between the conductive material and the second material. The barrier layer comprises a compound having silicon chemically bonded to both nitrogen and an organic material. In another aspect, the invention encompasses a composition of matter comprising silicon chemically bonded to both nitrogen and an organic material. The nitrogen is not bonded to carbon. In yet another aspect, the invention encompasses a semiconductor processing method. A semiconductive substrate is provided and a layer is formed over the semiconductive substrate. The layer comprises a compound having silicon chemically bonded to both nitrogen and an organic material.